JJMICROELECTRONICS

650V, 7.0A, 908mΩ N-channel Power SuperJunction MOSFET

JMH65R950MPLN

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant

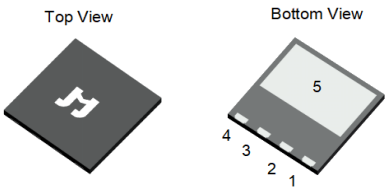
Applications

- SMPS with PFC
- Flyback and LLC topologies
- Silver ATX,adapter,TV,lighting,Telecom

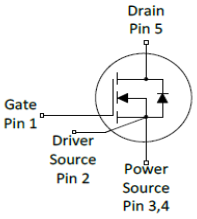
Product Summary

Parameters	Value	Unit
V_{DSS}	650	V
$V_{GS(th)_Typ}$	3.3	V
I_D(@V_{GS}=10V)	7.0	A
$R_{DS(ON)_Typ}$(@V_{GS}=10V	908	mΩ

RoHS



DFN8080-4L



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMH65R950MPLN-13	H65R950M	1	Tape&Reel	DFN8080-4L	3000	30000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		650	V
V_{GS}	Gate-to-Source Voltage		±30	V
I_D	Continuous Drain Current	T_C = 25°C	7.0	A
		T_C = 100°C	4.4	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		7.2	mJ
P_D	Power Dissipation	T_C = 25°C	115	W
		T_C = 100°C	46	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	44	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.1	

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±30V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.5	3.3	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 2A	-	908	950	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	4.6	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 325V, f = 1MHz	216	302	453	pF
C_{oss}	Output Capacitance		12	16	24	pF
C_{rss}	Reverse Transfer Capacitance		-	4.3	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 325V, I_D = 2A	-	7.9	-	nC
Q_{gs}	Gate Source Charge		-	2.1	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} =330V I_D= 2A, R_{GEN} = 24Ω	-	10	-	ns
t_r	Turn-On Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	34	-	ns
t_f	Turn-Off Fall Time		-	27	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	7.0	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	28	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 2A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 2A, di/dt = 100A/us	114	160	240	ns
Qrr	Body Diode Reverse Recovery Charge		-	1030	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=50V, V_{GS}=10V, R_G=25ohm, L=10mH, I_{AS}=1.2A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

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Typical Performance Characteristics

Figure 1: Power De-rating

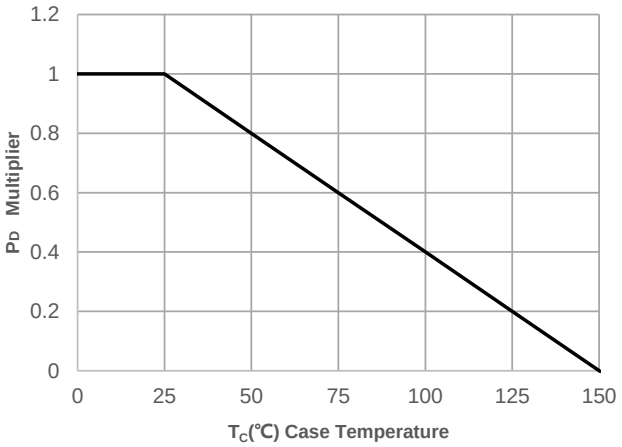


Figure 2: Current De-rating

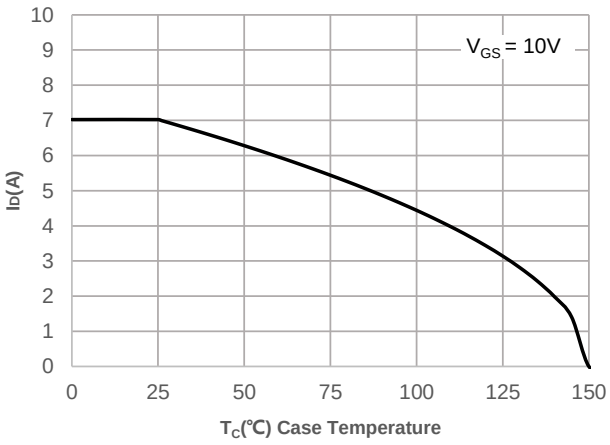


Figure 3: Normalized Maximum Transient Thermal Impedance

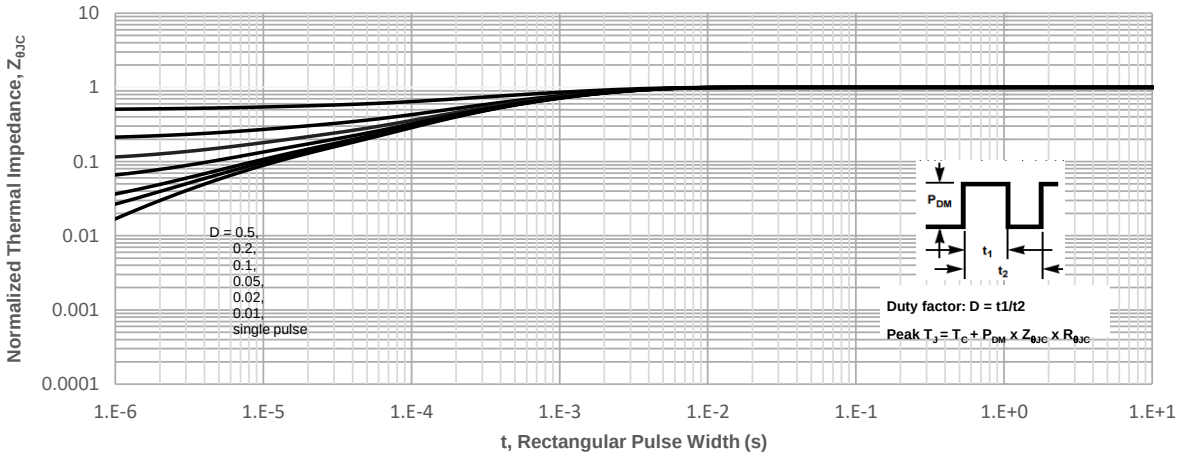
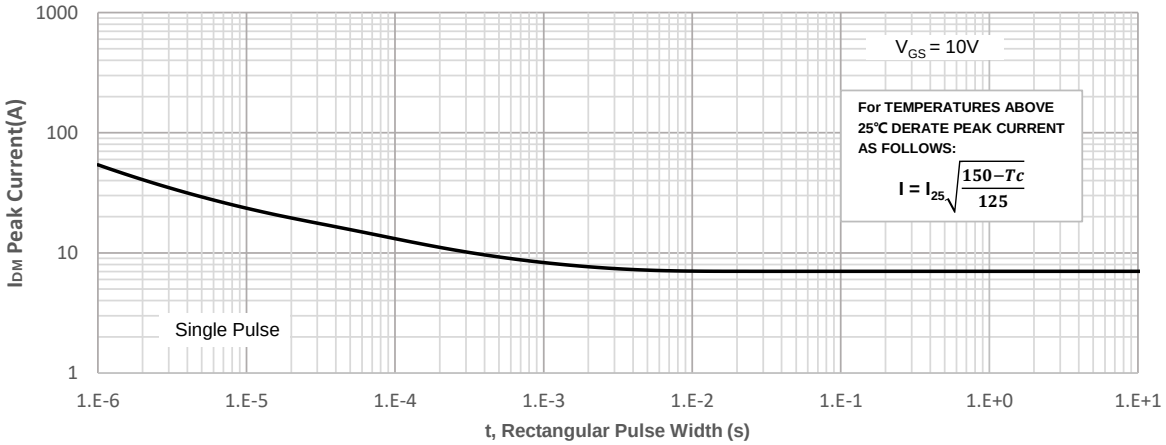


Figure 4: Peak Current Capacity



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Typical Performance Characteristics

Figure 5: Output Characteristics

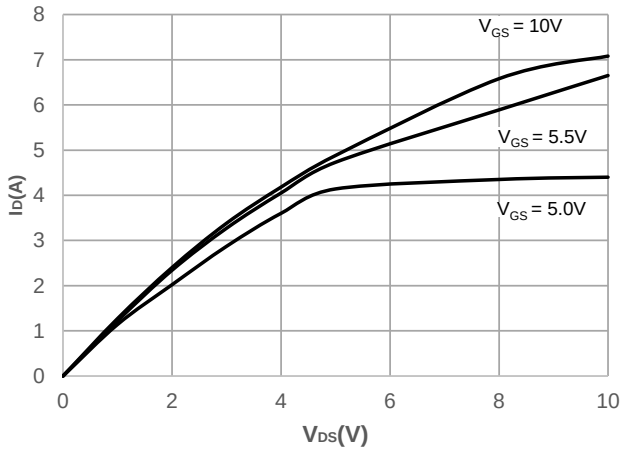


Figure 6: Typical Transfer Characteristics

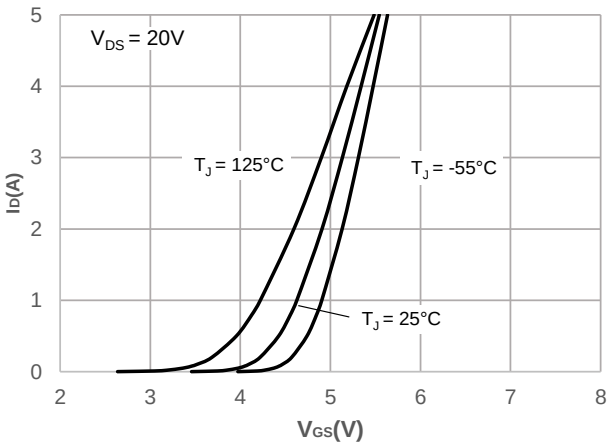


Figure 7: On-resistance vs. Drain Current

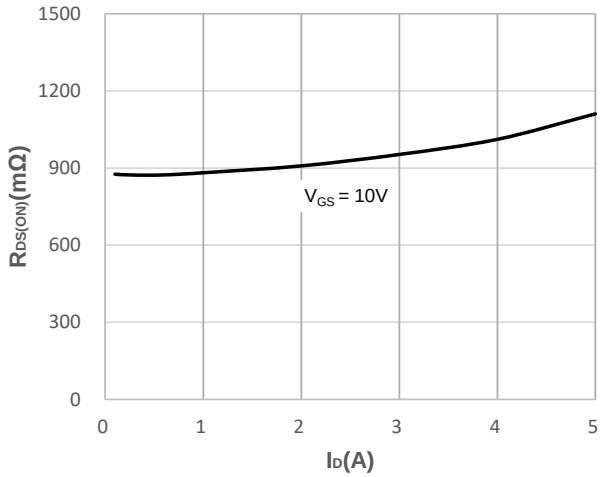


Figure 8: Body Diode Characteristics

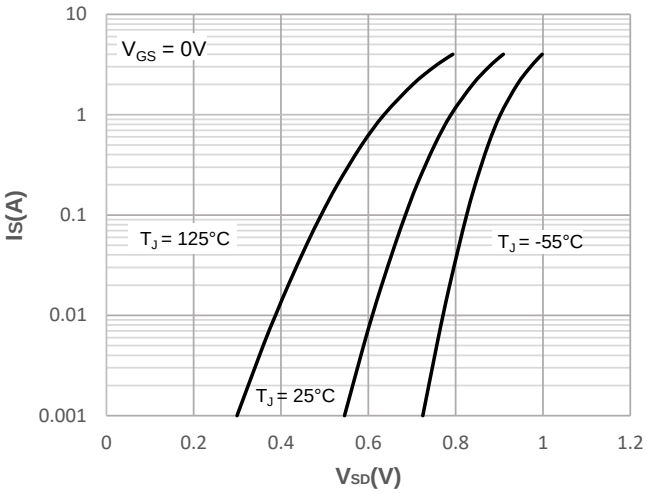


Figure 9: Gate Charge Characteristics

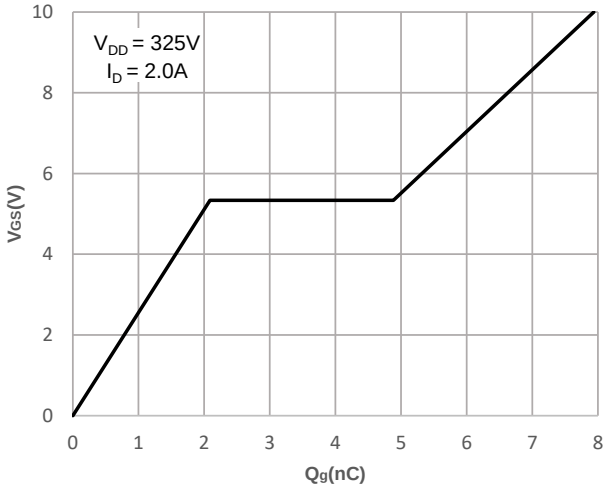
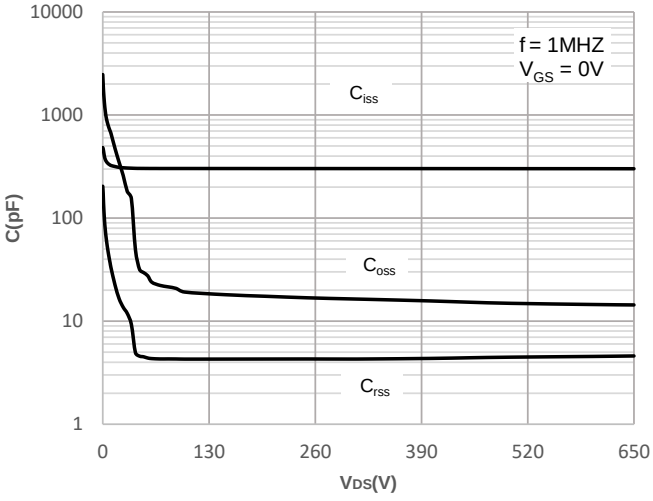


Figure 10: Capacitance Characteristics



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Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

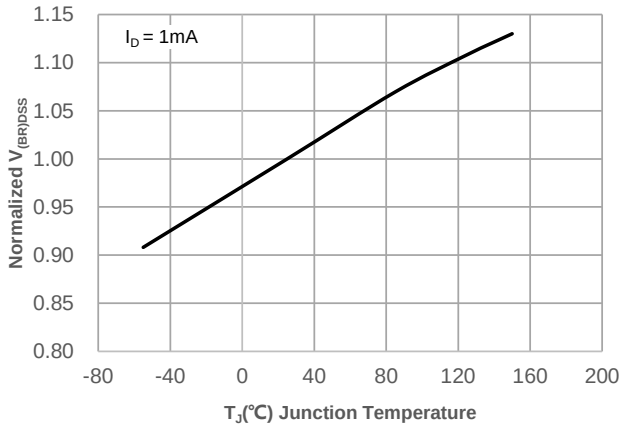


Figure 12: Normalized on Resistance vs. Junction Temperature

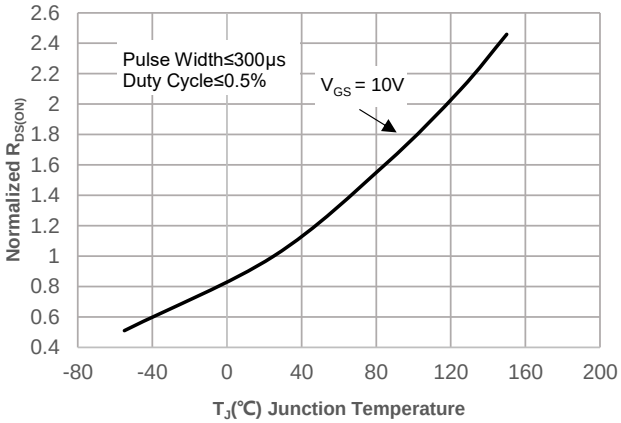


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

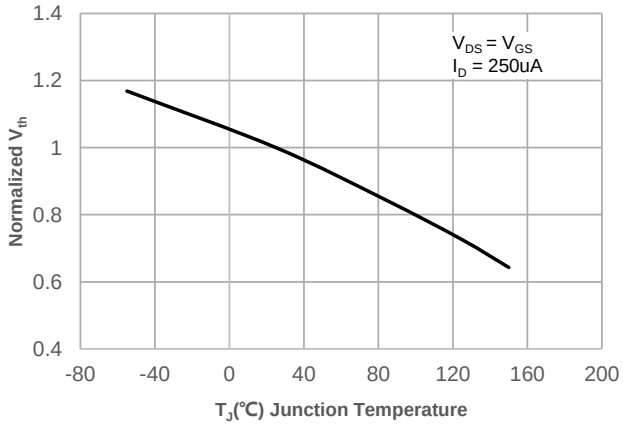


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

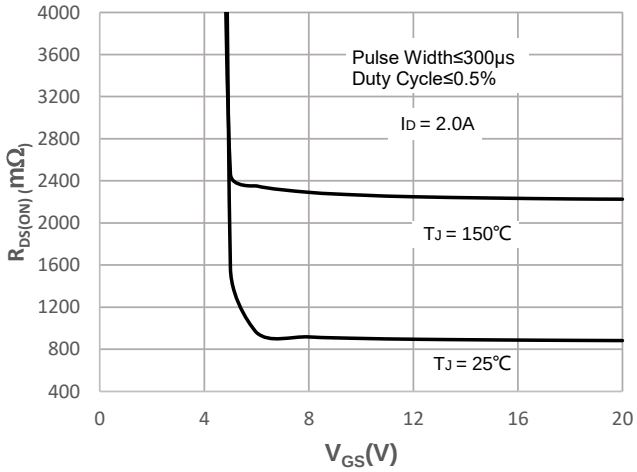
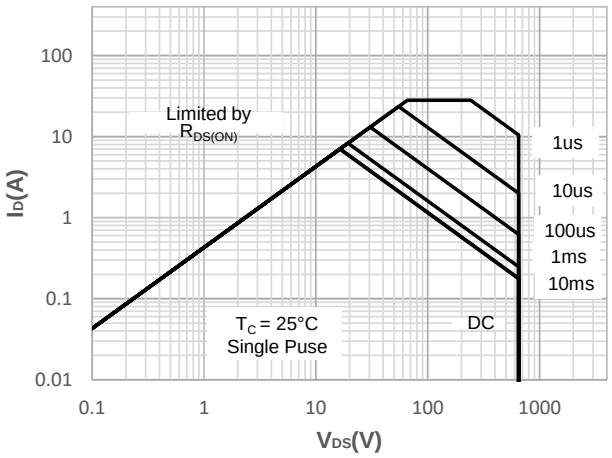


Figure 15: Maximum Safe Operating Area



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Test Circuit

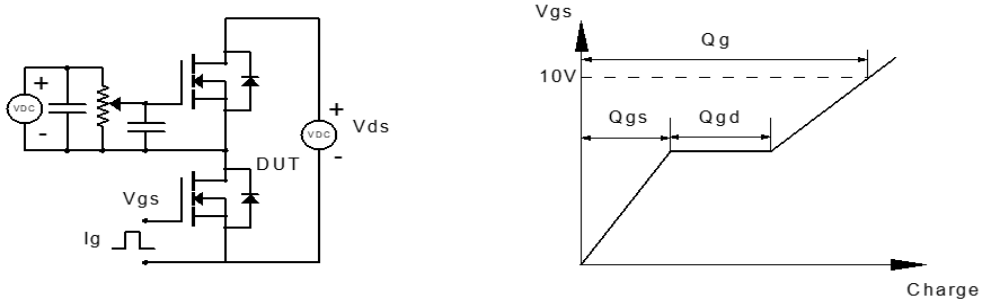


Figure 1: Gate Charge Test Circuit & Waveform

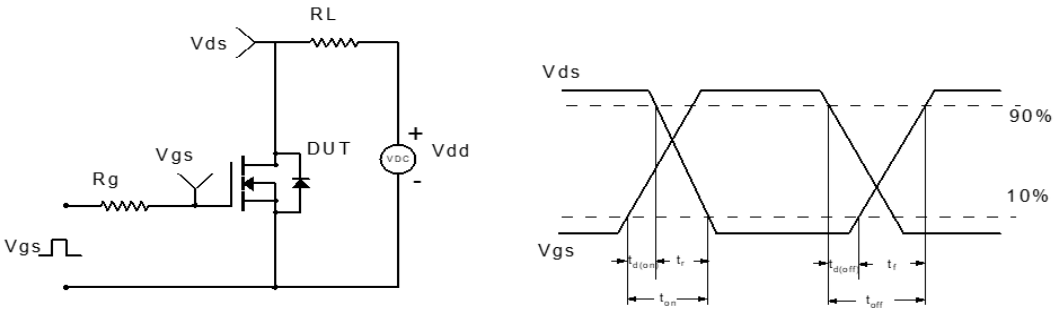


Figure 2: Resistive Switching Test Circuit & Waveform

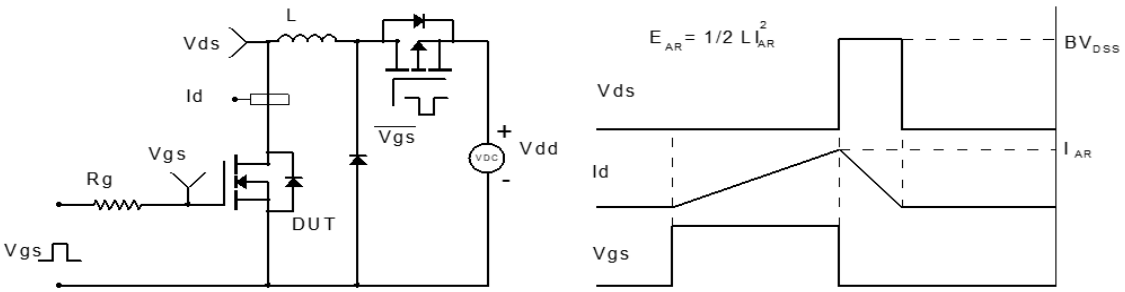


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

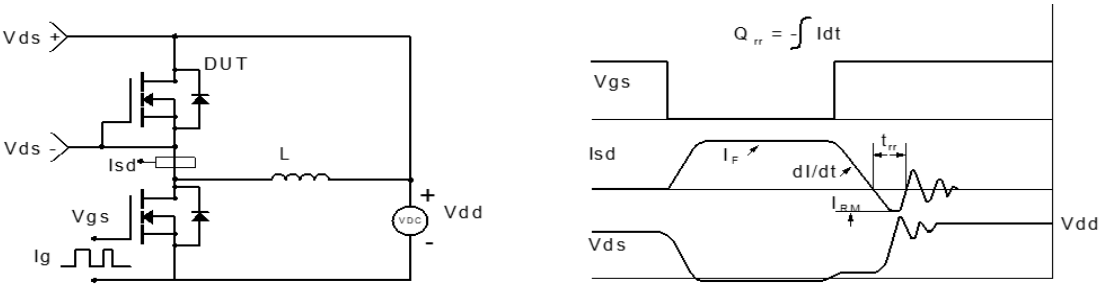
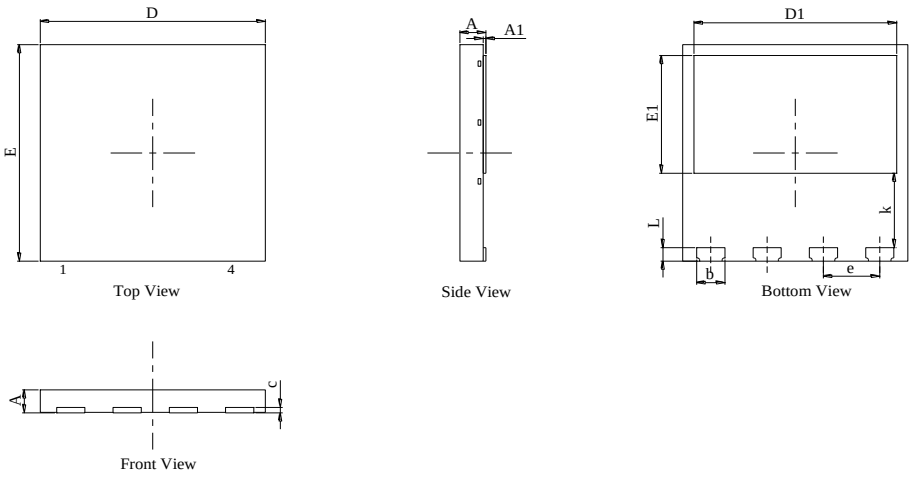


Figure 4: Diode Recovery Test Circuit & Waveform

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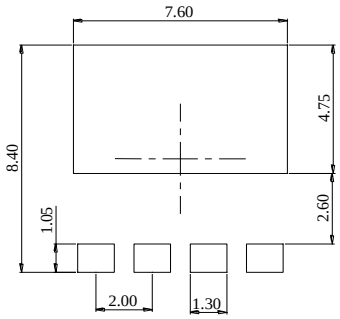
Package Mechanical Data(DFN8080-4L)

Package Outlines



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	--	--	0.05
b	0.95	1.00	1.05
c	--	0.20	--
D	7.90	8.00	8.10
D1	7.10	7.20	7.30
E	7.90	8.00	8.10
E1	4.25	4.35	4.45
L	0.40	0.50	0.60
k	2.75		
e	2.00 BSC		

Recommended Soldering Footprint



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